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LIST OF DOCUMENTS CITED BY APPLICANT
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Attorney Docket No.
5308-279

Serial No.
10/698,170

Applicant: Sei-Hyung Ryu

Filing Date: October 30, 2003

GAU: 2811

U.S. PATENT DOCUMENTS

Examiner Initials		Document No.	Date (m/d/y)	Name	Class	Subclass	Filing Date if Appropriate
LT	1	6,610,366	8/26/03	Lipkin	427	378	4/12/01
	2	6,316,791	11/13/01	Schormer et al.	257	77	—
	3	6,228,720	05/08/01	Kitabatake et al.	438	268	—
	4	5,877,045	3/2/99	Kapoor	438	151	—
	5	5,739,564	4/14/98	Kosa et al.	257	298	—
	6	5,587,870	12/24/96	Anderson et al.	361	313	—
	7	5,479,316	12/26/95	Smrtic et al.	361	322	—
	8	2002/0102358	8/1/02	Das et al.	472	376.2	10/26/01
	9	2002/0030191	3/14/02	Das et al.	257	77	6/12/01
LT	10	2002/0038891	4/4/02	Ryu et al.	257	350	6/24/01

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		Document Number	Date	Country	Class	Subclass	Translation (Yes/No)
LT	11	WO99/63591	12/9/99	PCT	—	—	—
LT	12	WO 98/02924	01/22/98	PCT	—	—	—
LT	13	WO 00/13236	03/09/00	PCT	—	—	—

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LT	14	Bhatnagar et al. "Comparison of 6H-SiC, 3C-SiC, and Si for Power Devices," <i>IEEE Transactions on Electron Devices</i> , Vol. 40, No. 3, March 1993, pp. 645-55.
	15	Baliga, <i>Power Semiconductor Devices</i> , Chapter 7, PWS Publishing, 1996
	16	United States Provisional Patent Application Serial No. 60/435,212
	17	United States Provisional Patent Application Serial No. 60/294,307
	18	United States Patent Application Serial No. 10/422,130
	19	Mutin, P. Herbert, "Control of the Composition and Structure of Silicon Oxycarbide and Oxynitride Glasses Derived from Polysiloxane Precursors," <i>Journal of Sol-Gel Science and Technology</i> , Vol. 14 (1999) pp. 27-38.
	20	del Prado et al. "Full Composition Range Silicon Oxynitride Films Deposited by ECR-PECVD at Room Temperatures," <i>Thin Solid Films</i> , Vol. 343-344 (1999) p. 437-440.
	21	Kobayashi et al. "Dielectric Breakdown and Current Conduction of Oxide/Nitride/Oxide Multi-Layer Structures," <i>1990 IEEE Symposium on VLSI Technology</i> , pp. 119-120.
	22	Ma et al. "Fixed and trapped charges at oxide-nitride-oxide heterostructure interfaces formed by remote plasma enhanced chemical vapor deposition," <i>J. Vac. Sci. Technol. B</i> , Vol. 11, No. 4, Jul/Aug 1993, pp. 1533-40.
	23	Dimitrijevic et al., "Nitridation of Silicon-Dioxide Films Grown on 6H Silicon Carbide", <i>IEEE Electronic Device Letters</i> , Vol. 18, No. 5, May 05, 1997, pp. 175-177.
	24	De Meo et al., "Thermal Oxidation of SiC in N ₂ O", <i>J. Electrochem. Soc.</i> , Vol. 141, 1994, pp. L150-L152.
	25	Dahlquist et al. "A 2.8kV, Forward Drop JBS Diode with Low Leakage," <i>Materials Science Forum</i> , Vols. 338-342, (2000) pp. 1179-82.
	26	Mondal et al. "An Integrated 500-V Power DSMOSFET/Antiparallel Rectifier Device with Improved Diode Reverse Recovery Characteristics," <i>IEEE Electron Device Letters</i> , Vol. 23, No. 9, September 2002, pp. 562-4.
	27	Motorola Power MOSFET Transistor Databook, 4th edition. Motorola, INC., 1989, pp. 2-5-4 - 2-5-7.
	28	Ryu et al. Article and Presentation: "27 mΩ-cm ² , 1.6 kV Power DiMOSFETs in 4H-SiC," <i>Proceedings of the 14 International Symposium on Power Semiconductor Devices & ICs 2002</i> , June 4-7, 2002, Santa Fe, NM.
	29	Chung et al. "Effects of anneals in ammonia on the interface trap density near the band edges in 4H-silicon carbide metal-oxide-semiconductor capacitors," <i>Applied Physics Letters</i> , Vol. 77, Nov. 27, 2000, pp. 3601-3.
LT	30	Williams et al. "Passivation of the 4H-SiC/SiO ₂ Interface with Nitric Oxide," <i>Materials Science Forum</i> , Vols. 389-393 (2002), pp. 967-72.

Examiner: /Long Tran/

Date Considered: 05/05/2006

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office				Attorney Docket Number: 5308-279		Serial No.: 10/698,170	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Sei-Hyung Ryu			
				Filing Date: October 30, 2003		Group 281	
U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
LT	1.	6,429,041	08/06/2002	Ryu et al.	438	105	
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		Document Number	Date	Country	Class	Subclass	Translation Yes No
LT	2.	JP 03034466	02/14/1991	Japan	—	—	Abstract
LT	3.	JP 01117363	05/10/1989	Japan	—	—	Abstract
LT	4.	EP 1058317 A2	12/06/2000	EPO	—	—	
LT	5.	DE 19809554 A1	09/10/1998	Germany	—	—	
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LT	6.	Copy of International Search Report for PCT/US03/38490 mailed 08/05/2004					

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FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Attorney Docket Number: 5308-279		Serial No.: To Be Assigned <div style="text-align: right; font-size: 1.2em;">10/628070</div>	
				Applicants: Sei-Hyung Ryu			
				Filing Date: Concurrently Herewith		Group Unknown 2878	

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Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
UET	1	6,593,620	7/15/03	Hsieh et al.	257	335	—
	2	6,455,892	9/02	Okuno	257	77	—
	3	6,344,663 B1	2/5/02	Slater, Jr. et al.	257	77	—
	4	6,297,172	10/2/01	Kashiwagi	438	773	—
	5	6,246,076 B1	6/12/01	Lipkin et al.	257	77	—
	6	6,239,463	5/29/01	Williams et al.	257	328	—
	7	6,238,967 B1	5/29/01	Shiho et al.	438	244	—
	8	6,221,700	4/24/01	Okuno et al.	438	151	—
	9	6,211,035	4/01	Moise et al.	438	396	—
	10	6,204,203	3/01	Narwanker et al.	438	785	—
	11	6,190,973 B1	2/20/01	Berg et al.	438	275	—
	12	6,165,822	12/26/00	Okuno et al.	438	142	—
	13	6,136,728	10/24/00	Wang	—	—	—
	14	6,117,735	9/12/00	Ueno	438	268	—
	15	6,107,142	8/22/00	Suvorov et al.	438	285	—
	16	6,100,169	8/8/00	Suvorov et al.	438	519	—
	17	6,096,607	8/1/00	Ueno	438	522	—
	18	6,063,698	5/16/00	Tseng et al.	—	—	—
	19	6,054,352	4/25/00	Ueno	438	268	—
	20	6,048,766	4/11/00	Gardner et al.	—	—	—
	21	6,028,012	2/22/00	Wang	—	—	—
UET	22	6,025,608	2/15/00	Harris et al.	257	77	—
	23	5,972,801	10/26/99	Lipkin et al.	438	770	—
UET	24	5,972,801	10/26/99	Lipkin et al.	438	770	—
	25	5,960,289	9/28/99	Tsui et al.	438	257	—
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Filing Date: Concurrently Herewith				Group Unknown <i>2878</i>			

<i>UKT</i>	28	5,837,572	11/17/98	Gardner et al.	438	199	—
	29	5,763,905	6/9/98	Harris	257	77	—
	30	5,726,463	3/10/98	Brown et al.	257	77	—
	31	5,510,630	4/23/96	Agarwal	257	77	—
	32	5,506,421	4-9-96	Palmour	257	77	—
	33	5,184,199	2/2/93	Fujii et al.	29	10	—
	34	5,170,455	12/8/92	Goossen et al.	385	89	—
	35	5,170,231	12/92	Fujii et al.	257	77	—
	36	4,875,083	10/17/89	Palmour	357	23.6	—
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	38	3,924,024	12/2/75	Naber et al.	427	95	—
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	42	DE 10036208	2/14/02	Germany	—	—	Abstract
	43	DE 198 09 554	9/10/98	Germany	—	—	Abstract
	44	DE 19900171	12/26/00	Germany	—	—	Abstract
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	46	JP 08264766	10/11/96	Japan	—	—	Abstract
	47	JP 09205202	8/5/97	Japan	—	—	Abstract
	48	JP 11191559	7/13/99	Japan	—	—	Abstract
	49	JP 11238742	8/31/99	Japan	—	—	Abstract
	50	JP 11261061	9/24/99	Japan	—	—	Abstract
	51	JP 11266017	9/28/99	Japan	—	—	Abstract
	52	JP 11274487	10/8/99	Japan	—	—	Abstract
	53	JP 2000049167	2/18/00	Japan	—	—	Abstract
	54	JP 2000082812	3/21/00	Japan	—	—	Abstract

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LT	2.	DE 198 32 329	2/4/1999	Germany	H01L	21/334	
LT	3.	WO 01/78134	10/18/2001	PCT	H01L	21/76	
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